



CMUDM8001

**SURFACE MOUNT
P-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET**

ULTRAmiTM**SOT-523 CASE****APPLICATIONS:**

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Powered Portable Equipment

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	10	V
Continuous Drain Current (Steady State)	I_D	100	mA
Continuous Drain Current	I_D	200	mA
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}	$V_{GS}=10\text{V}, V_{DS}=0\text{V}$			1.0	μA
I_{GSSR}	$V_{GS}=10\text{V}, V_{DS}=0\text{V}$			1.0	μA
I_{DSS}	$V_{DS}=20\text{V}, V_{GS}=0\text{V}$			1.0	μA
BV_{DSS}	$V_{GS}=0\text{V}, I_D=100\mu\text{A}$	20			V
$V_{GS(\text{th})}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.6		1.1	V
$r_{DS(\text{ON})}$	$V_{GS}=4.0\text{V}, I_D=10\text{mA}$			8.0	Ω
$r_{DS(\text{ON})}$	$V_{GS}=2.5\text{V}, I_D=10\text{mA}$			12	Ω
$r_{DS(\text{ON})}$	$V_{GS}=1.5\text{V}, I_D=1.0\text{mA}$			45	Ω
g_{fs}	$V_{DS}=10\text{V}, I_D=100\text{mA}$	100			mS
C_{rss}	$V_{DS}=3.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$		15		pF
C_{iss}	$V_{DS}=3.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$	45			pF
C_{oss}	$V_{DS}=3.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$	15			pF
t_{on}	$V_{DD}=3.0\text{V}, V_{GS}=2.5\text{V}, I_D=10\text{mA}$	35			ns
t_{off}	$V_{DD}=3.0\text{V}, V_{GS}=2.5\text{V}, I_D=10\text{mA}$	80			ns

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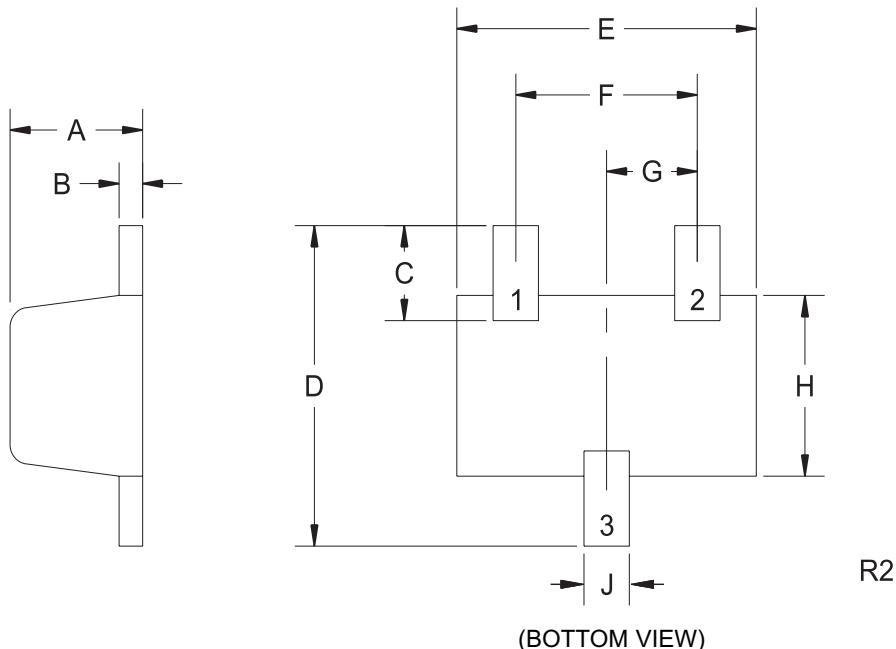
DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMUDM8001 is an Enhancement-mode P-Channel Field Effect Transistor, manufactured by the P-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. This MOSFET offers Low $r_{DS(\text{on})}$ and Low Threshold Voltage.

MARKING CODE: C8A**FEATURES:**

- Power Dissipation 250mW
- Low $r_{DS(\text{on})}$
- Low Threshold Voltage
- Logic Level Compatible
- Small, SOT-523 Surface Mount Package
- Complementary Device: CMUDM7001

SOT-523 - MECHANICAL OUTLINE



(BOTTOM VIEW)

LEAD CODE:
1) GATE
2) SOURCE
3) DRAIN

MARKING CODE: C8A

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.023	0.031	0.58	0.78
B	0.002	0.008	0.04	0.20
C	0.013	0.021	0.34	0.54
D	0.059	0.067	1.50	1.70
E	0.059	0.067	1.50	1.70
F	0.035	0.043	0.90	1.10
G	0.020		0.50	
H	0.031	0.039	0.78	0.98
J	0.010	0.014	0.25	0.35

SOT-523 (REV: R2)

R0 (4-March 2008)